

WHAT IS CLAIMED IS:

1. A semiconductor light-emitting device comprising:
a semiconductor light-emitting device chip including a chip
substrate and a stack formed of semiconductor layers stacked on a surface of
said chip substrate; and

5 a mount member having a mount surface, wherein
said semiconductor light-emitting device chip is connected to the
mount surface of said mount member with said stack facing said mount
surface, and

10 said mount member includes a material higher in thermal expansion
coefficient than a material for said chip substrate.

2. A semiconductor light-emitting device comprising:
a semiconductor light-emitting device chip including a chip
substrate and a stack formed of semiconductor layers stacked on a surface of
said chip substrate; and

5 a mount member having a mount surface, wherein
said semiconductor light-emitting device chip is connected to the
mount surface of said mount member with said stack facing said mount
surface, and

10 said mount surface is curved to protrude and said semiconductor
light-emitting device chip is curved along and connected to said mount
surface.

3. The semiconductor light-emitting device according to claim 1,
wherein
said chip substrate includes nitride-based compound semiconductor
and said stack includes nitride-based compound semiconductor.

4. The semiconductor light-emitting device according to claim 3,
wherein
said mount member includes at least one of iron and copper.

5. The semiconductor light-emitting device according to claim 1,
wherein

said mount surface and said stack are connected by solder and said
solder includes at least one selected from the group consisting of In, Sn, Pb
and Au.

5

20100907 22:28:00